

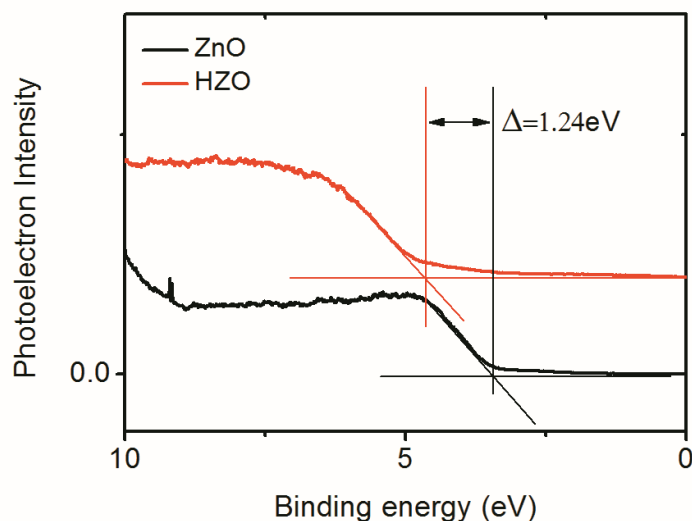
## Electronic supplementary information:

### Origin of highly-stable conductivity of H plasma exposed ZnO films

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**Figure S1.** UPS spectra of ZnO (black) and HZO (red) films. After H plasma treatment, spectra moved leftward about 1.24 eV, indicating a patent increase of Fermi Energy level.